**30V N-CHANNEL ENHANCEMENT MODE MOSFET**
**PowerDI3333-8**

## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$ Max | $I_D$ Max<br>$T_C$ = +25°C |
|---|---|---|
| 30V | 1.7mΩ @ $V_{GS}$ = 10V | 100A |
| | 2.8mΩ @ $V_{GS}$ = 4.5V | 100A |

## Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

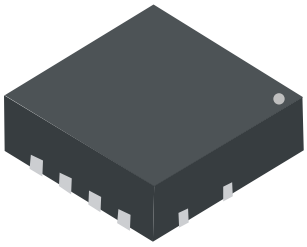
## Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Excellent $Q_{gd}$ × $R_{DS(ON)}$ Product (FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

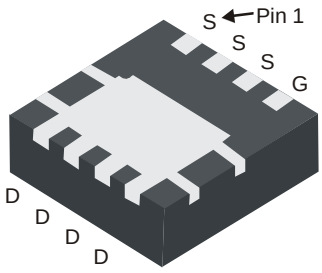
## Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish – Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (Approximate)

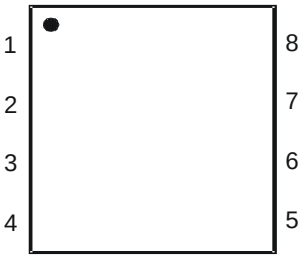
PowerDI3333-8



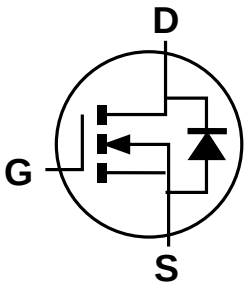
Top View




Bottom View




Top View



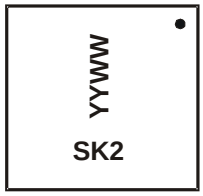

Equivalent Circuit

## Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---|---|---|
| DMT32M5LFG-7 | PowerDI3333-8 | 2,000/Tape & Reel |
| DMT32M5LFG-13 | PowerDI3333-8 | 3,000/Tape & Reel |

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information




SK2 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

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## Maximum Ratings (@$T_C$ = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 30 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±20 | V |
| Continuous Drain Current (Note 6) $V_{GS}$ = 10V | $T_C$ = +25°C<br>$T_C$ = +70°C | $I_D$ | 100<br>100 | A |
| Continuous Drain Current (Note 5) $V_{GS}$ = 10V | $T_A$ = +25°C<br>$T_A$ = +70°C | $I_D$ | 30<br>24 | A |
| Maximum Continuous Body Diode Forward Current (Note 5) | | $I_S$ | 2.8 | A |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%) | | $I_{DM}$ | 350 | A |
| Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%) | | $I_{SM}$ | 350 | A |
| Avalanche Current, L = 0.1mH | | $I_{AS}$ | 46.7 | A |
| Avalanche Energy, L = 0.1mH | | $E_{AS}$ | 109 | mJ |

## Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|---|---|---|---|---|
| Total Power Dissipation (Note 5) | $T_A$ = +25°C | $P_D$ | 2.3 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | | $R_{\theta JA}$ | 54 | °C/W |
| Total Power Dissipation (Note 6) | $T_C$ = +25°C | $P_D$ | 50 | W |
| Thermal Resistance, Junction to Case (Note 6) | | $R_{\theta JC}$ | 2.5 | °C/W |
| Operating and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to +150 | °C |

## Electrical Characteristics (@$T_J$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | 30 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 1mA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | — | — | 1 | µA | $V_{DS}$ = 24V, $V_{GS}$ = 0V |
| | | — | — | 10 | | $V_{DS}$ = 30V, $V_{GS}$ = 0V |
| Gate-Source Leakage | $I_{GSS}$ | — | — | ±10 | µA | $V_{GS}$ = 20V, $V_{DS}$ = 0V<br>$V_{GS}$ = -16V, $V_{DS}$ = 0V |
| **ON CHARACTERISTICS** (Note 7) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 1 | 1.4 | 3 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250µA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 1.4 | 1.7 | mΩ | $V_{GS}$ = 10V, $I_D$ = 20A |
| | | — | 2.1 | 2.8 | | $V_{GS}$ = 4.5V, $I_D$ = 15A |
| | | — | 1.9 | 2.6 | mΩ | $V_{GS}$ = 10V, $I_D$ = 20A,<br>$T_J$ = +125°C (Note 8) |
| Diode Forward Voltage | $V_{SD}$ | — | 0.7 | 1 | V | $V_{GS}$ = 0V, $I_S$ = 2A |
| **DYNAMIC CHARACTERISTICS** (Note 8) | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 4066 | — | pF | $V_{DS}$ = 15V, $V_{GS}$ = 0V,<br>f = 1MHz |
| Output Capacitance | $C_{oss}$ | — | 1736 | — | | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 333 | — | | |
| Gate Resistance | $R_g$ | — | 0.71 | — | Ω | $V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz |
| Total Gate Charge ($V_{GS}$ = 4.5V) | $Q_g$ | — | 34 | — | nC | $V_{DS}$ = 15V, $I_D$ = 20A |
| Total Gate Charge ($V_{GS}$ = 10V) | $Q_g$ | — | 67.7 | — | | |
| Gate-Source Charge | $Q_{gs}$ | — | 8 | — | | |
| Gate-Drain Charge | $Q_{gd}$ | — | 15 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 7.2 | — | ns | $V_{DD}$ = 15V, $V_{GS}$ = 10V,<br>$R_G$ = 3Ω, $I_D$ = 20A |
| Turn-On Rise Time | $t_R$ | — | 13.2 | — | | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 37.4 | — | | |
| Turn-Off Fall Time | $t_F$ | — | 23.9 | — | | |
| Bodyy Diode Reverse Recovery Time | $t_{RR}$ | — | 28.7 | — | ns | $I_F$ = 15A, di/dt = 500A/µs |
| Body Diode Reverse Recovery Charge | $Q_{RR}$ | — | 45.8 | — | nC | |

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

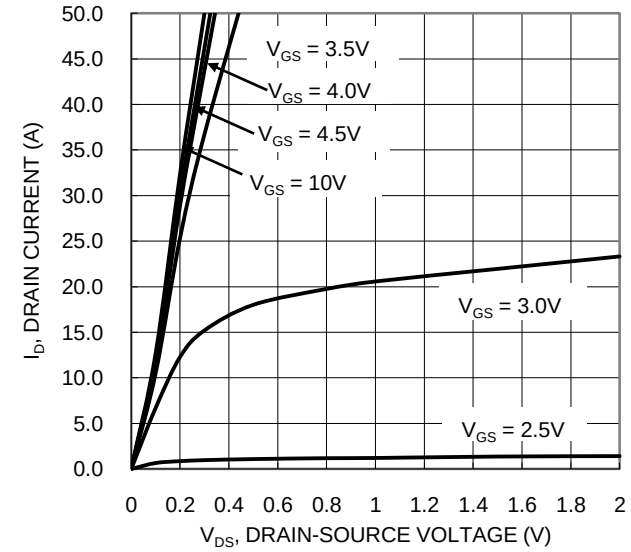



Figure 1. Typical Output Characteristic

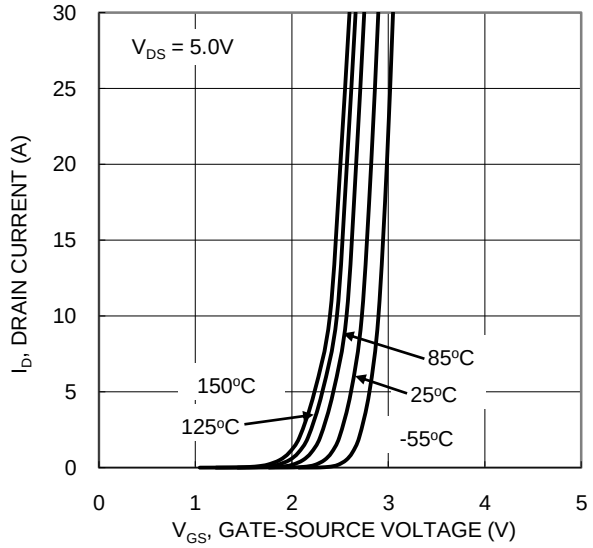



Figure 2. Typical Transfer Characteristic

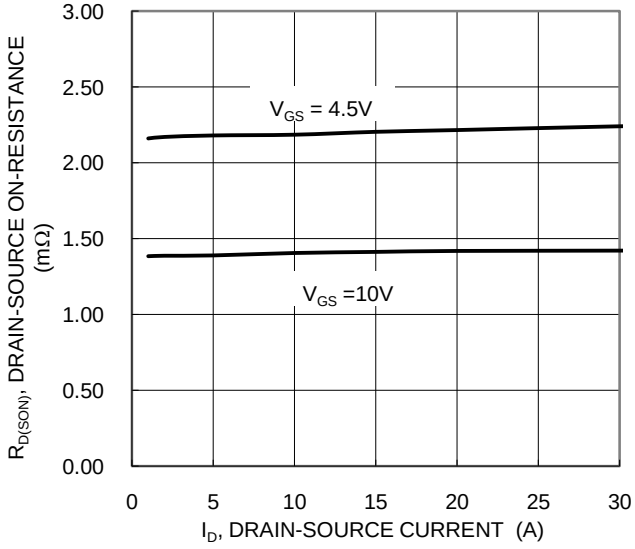



Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

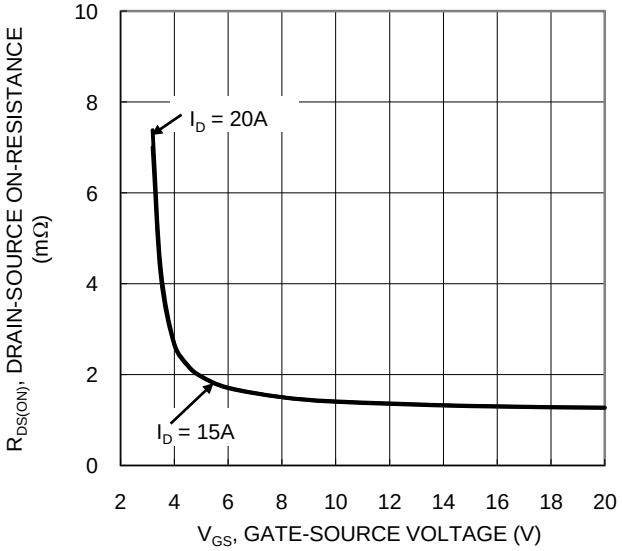



Figure 4. Typical Transfer Characteristic

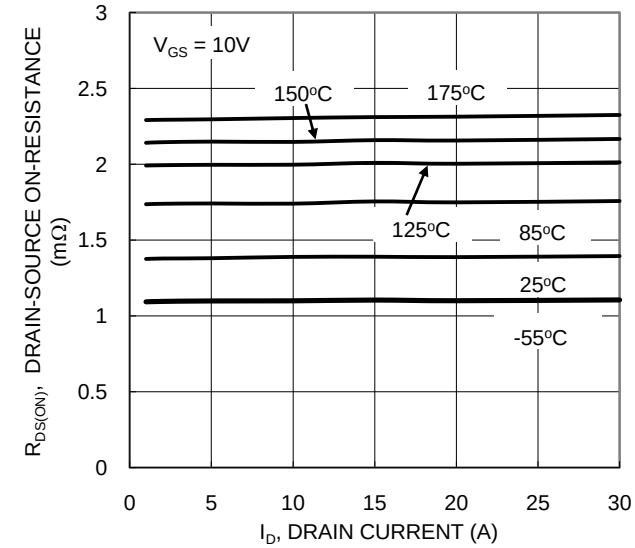



Figure 5. Typical On-Resistance vs. Drain Current and Temperature

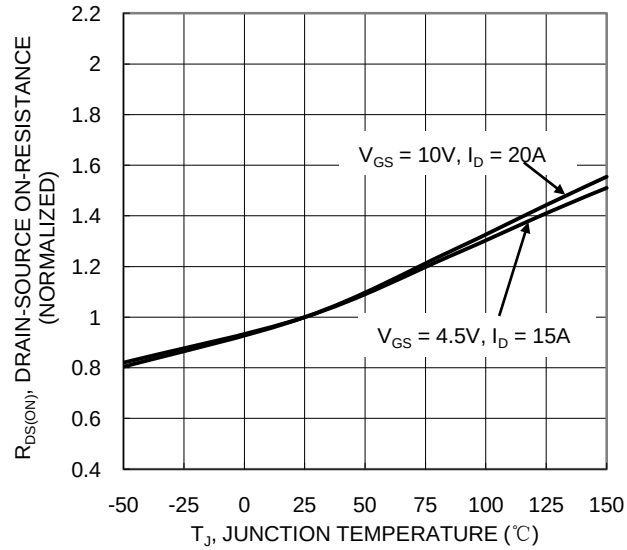



Figure 6. On-Resistance Variation with Temperature

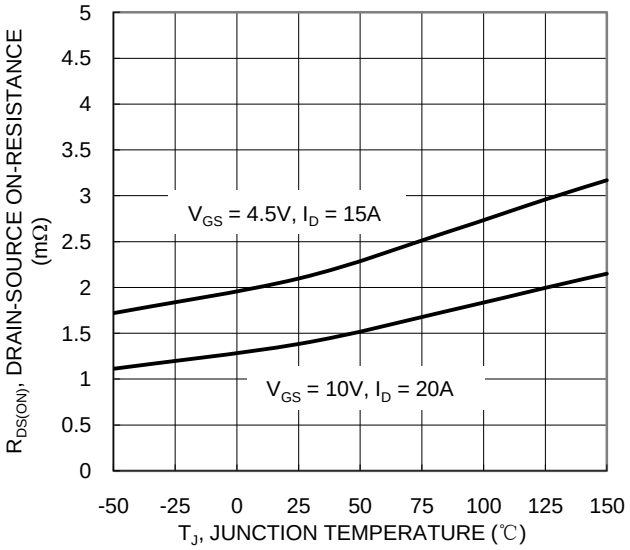



Figure 7. On-Resistance Variation with Temperature

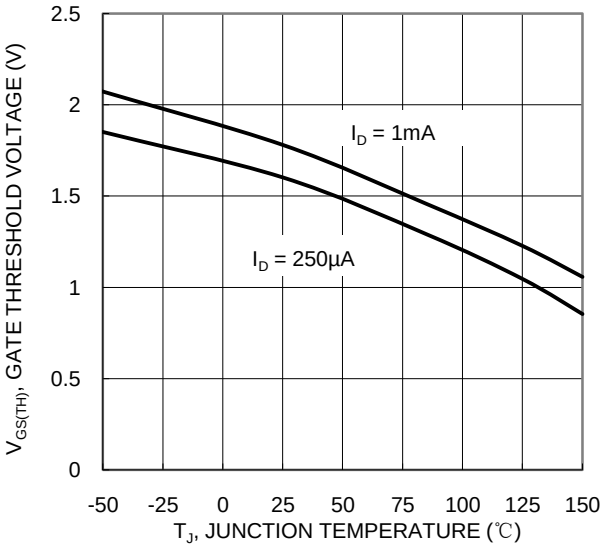



Figure 8. Gate Threshold Variation vs. Junction Temperature

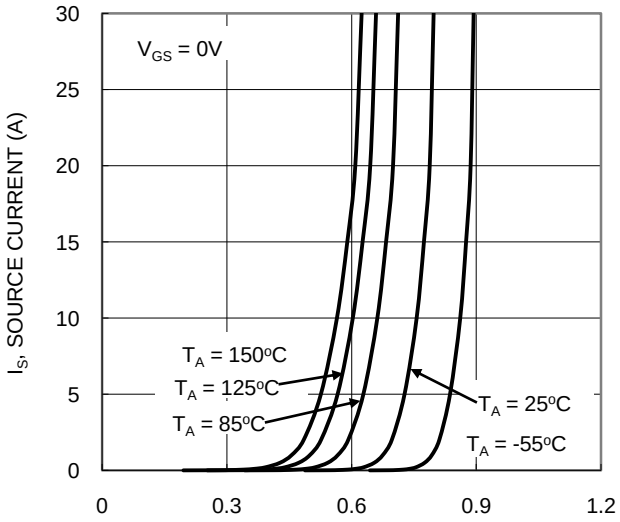



Figure 9. Diode Forward Voltage vs. Current

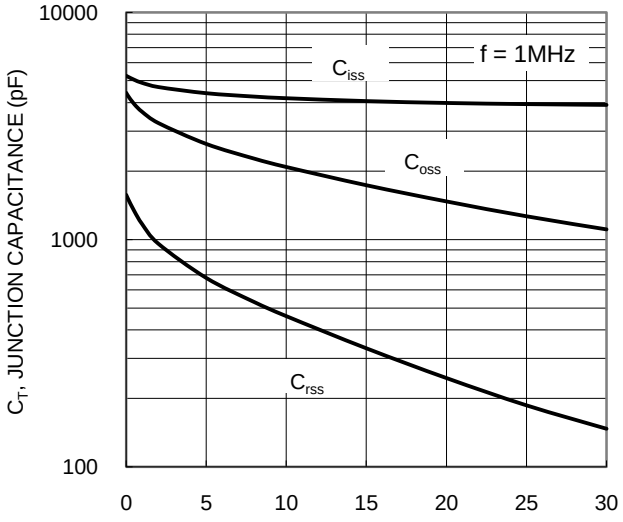



Figure 10. Typical Junction Capacitance

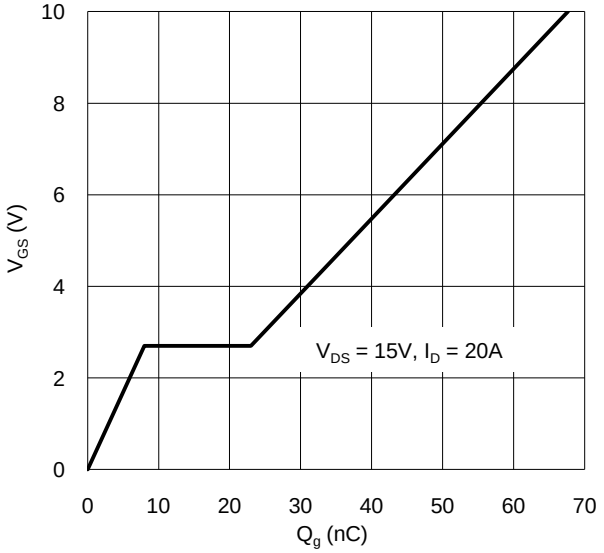



Figure 11. Gate Charge

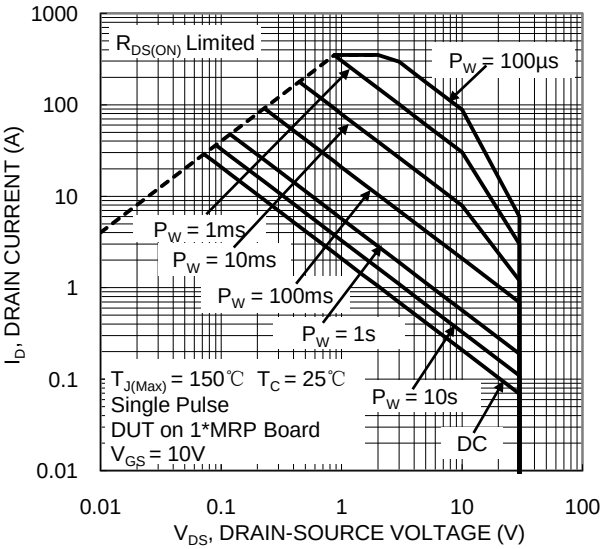



Figure12. SOA, Safe Operation Area

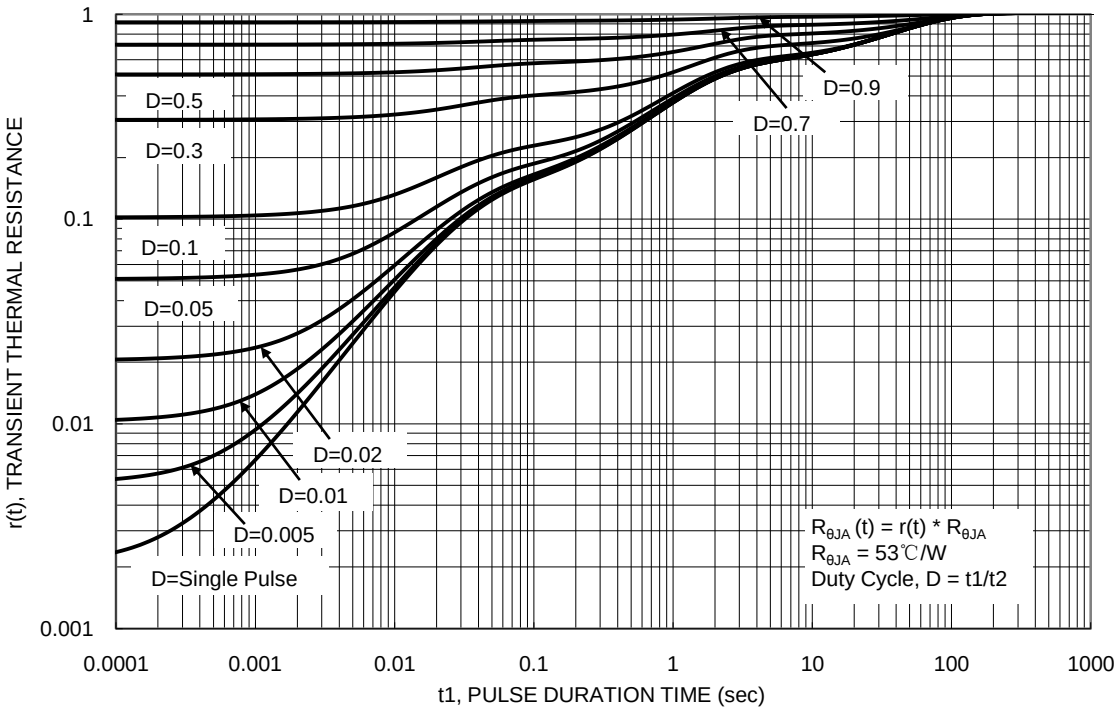
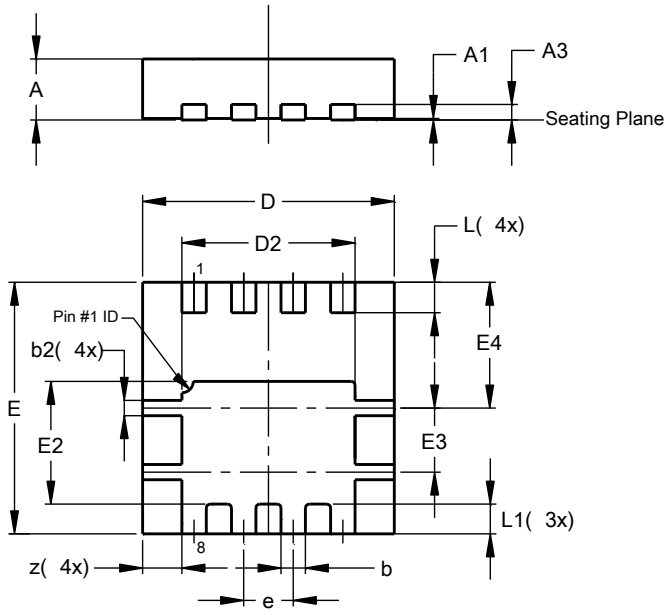



Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

**PowerDI3333-8**

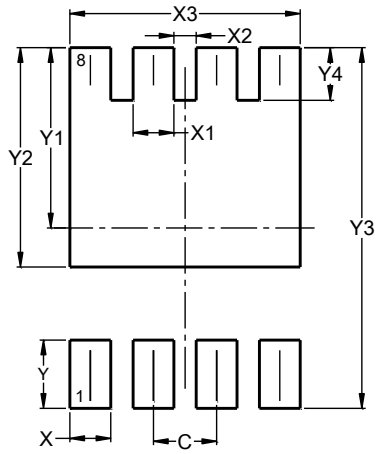



| PowerDI3333-8 | | | |
|---|---|---|---|
| **Dim** | **Min** | **Max** | **Typ** |
| **A** | 0.75 | 0.85 | 0.80 |
| **A1** | 0.00 | 0.05 | 0.02 |
| **A3** | – | – | 0.203 |
| **b** | 0.27 | 0.37 | 0.32 |
| **b2** | 0.15 | 0.25 | 0.20 |
| **D** | 3.25 | 3.35 | 3.30 |
| **D2** | 2.22 | 2.32 | 2.27 |
| **E** | 3.25 | 3.35 | 3.30 |
| **E2** | 1.56 | 1.66 | 1.61 |
| **E3** | 0.79 | 0.89 | 0.84 |
| **E4** | 1.60 | 1.70 | 1.65 |
| **e** | – | – | 0.65 |
| **L** | 0.35 | 0.45 | 0.40 |
| **L1** | – | – | 0.39 |
| **z** | – | – | 0.515 |
| **All Dimensions in mm** | | | |

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

**PowerDI3333-8**




| Dimensions | Value (in mm) |
|---|---|
| **C** | 0.650 |
| **X** | 0.420 |
| **X1** | 0.420 |
| **X2** | 0.230 |
| **X3** | 2.370 |
| **Y** | 0.700 |
| **Y1** | 1.850 |
| **Y2** | 2.250 |
| **Y3** | 3.700 |
| **Y4** | 0.540 |

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